

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	4.0	A
		T <sub>A</sub> = +70°C		3.5	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	35	A
Maximum Body Diode Forward Current (Note 6)			I <sub>S</sub>	1.5	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.76	W
	T <sub>A</sub> = +70°C		0.48	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R <sub>θJA</sub>	165	°C/W
	t < 10s	R <sub>θJA</sub>	114	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.2	W
	T <sub>A</sub> = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R <sub>θJA</sub>	100	°C/W
	t < 10s	R <sub>θJA</sub>	69	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	—	1.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	36	45	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.0A V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.5A V <sub>GS</sub> = 3.0V, I <sub>D</sub> = 3.0A V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2.8A
			38	50		
			42	53		
			44	55		
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.25A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	676	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	54	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	42	—	pF	
Gate Resistance	R <sub>g</sub>	—	15.5	—	Ω	V <sub>DS</sub> = V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	7.3	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	17.2	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	1.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.9	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	2.0	—	ns	
Turn-On Rise Time	t <sub>r</sub>	—	5.5	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6Ω
Turn-Off Delay Time	t <sub>D(off)</sub>	—	152	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	32	—	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  - Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

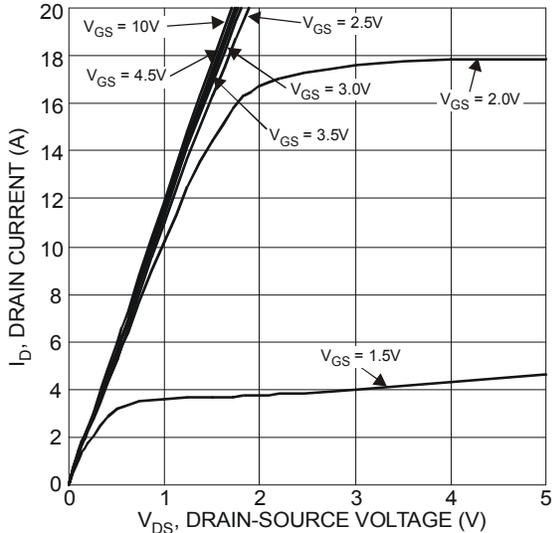


Figure 1 Typical Output Characteristics

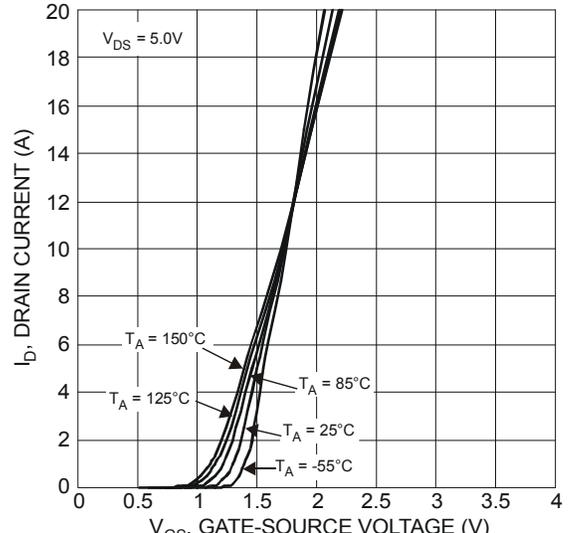


Figure 2 Typical Transfer Characteristics

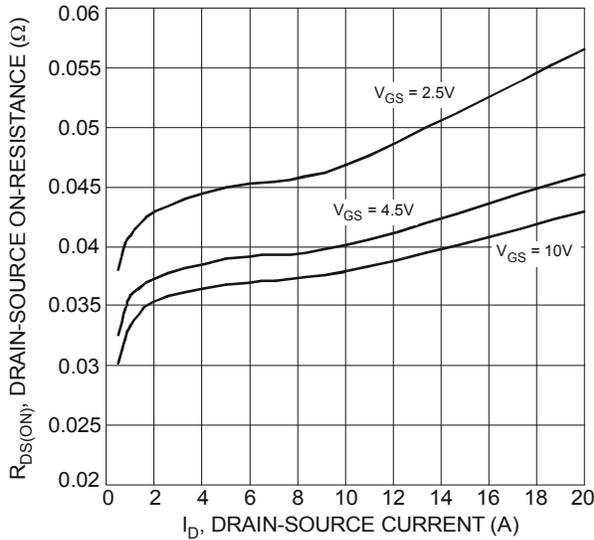


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

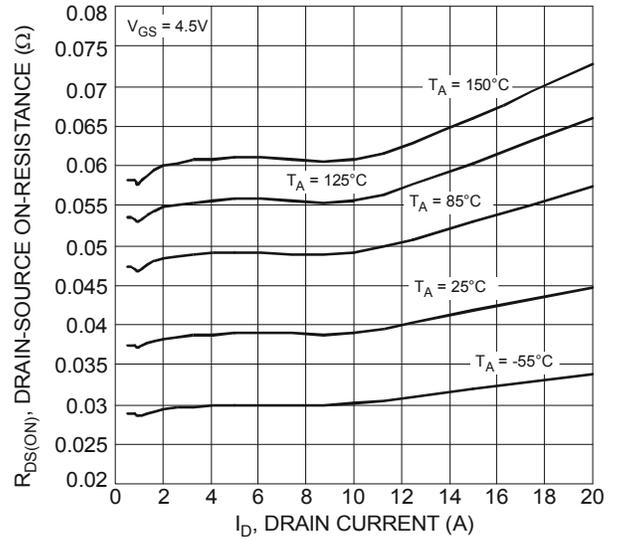


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

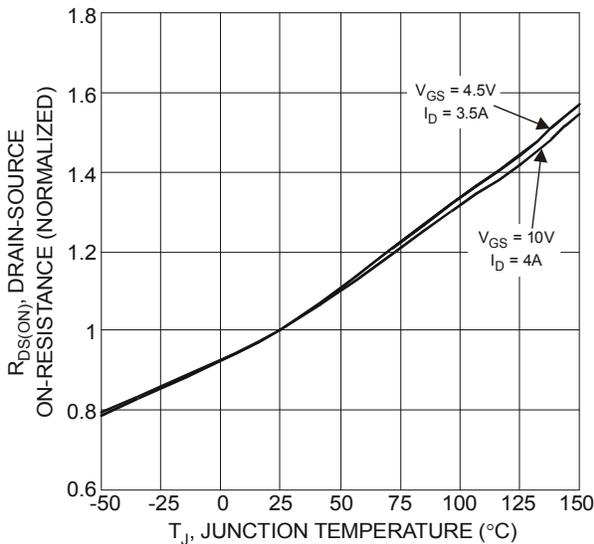


Figure 5 On-Resistance Variation with Temperature

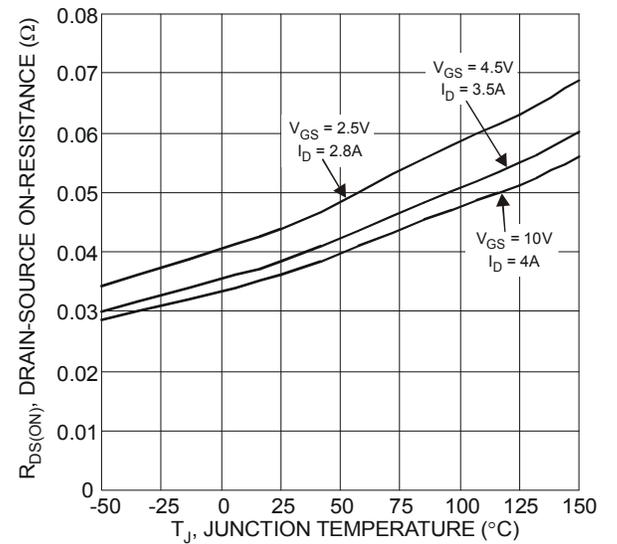


Figure 6 On-Resistance Variation with Temperature

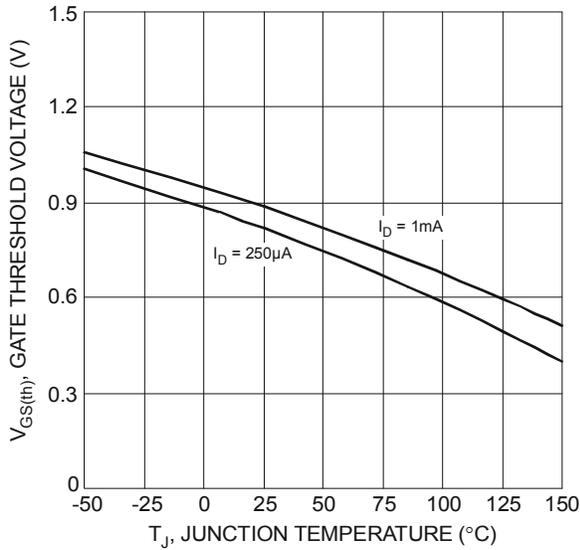


Figure 7 Gate Threshold Variation vs. Ambient Temperature

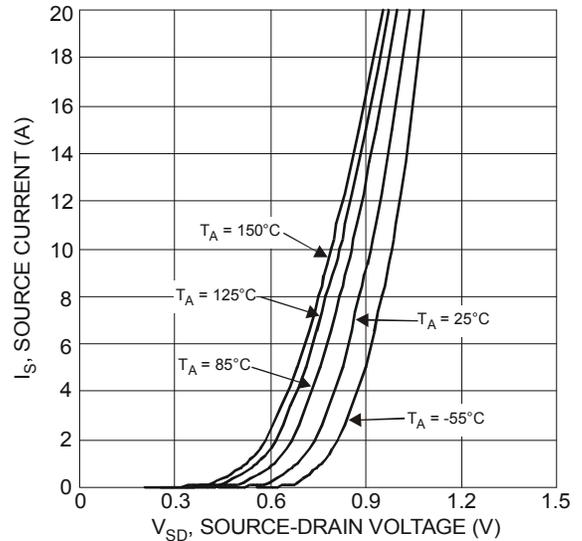


Figure 8 Diode Forward Voltage vs. Current

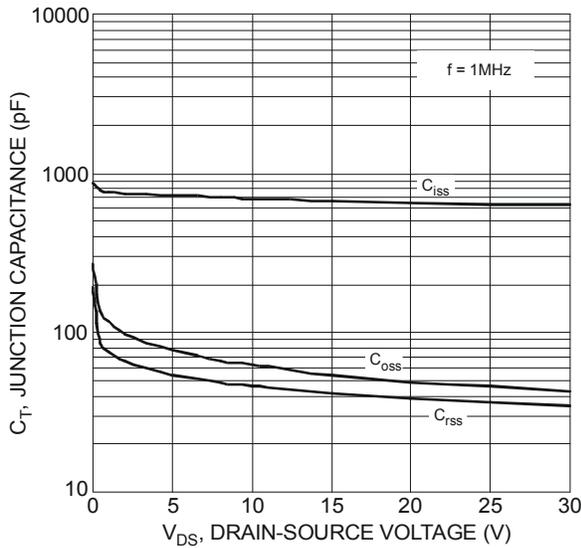


Figure 9 Typical Junction Capacitance

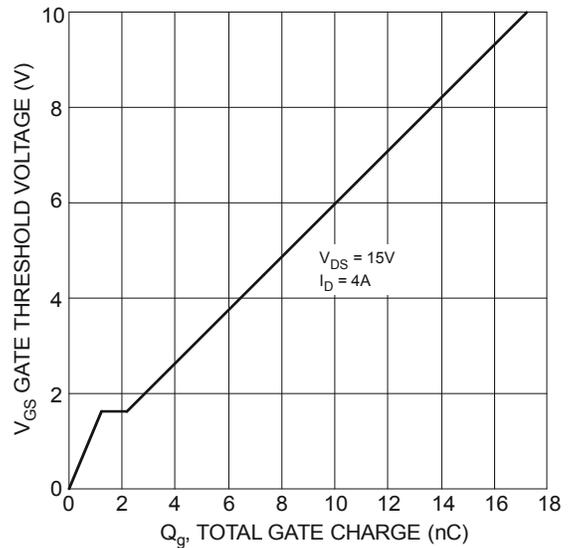


Figure 10 Gate Charge

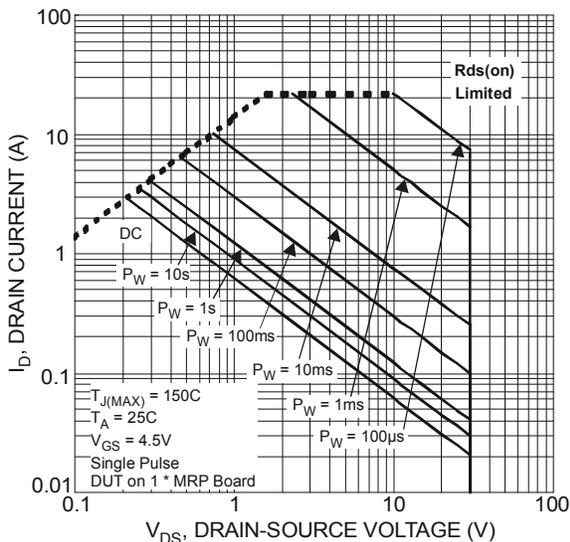
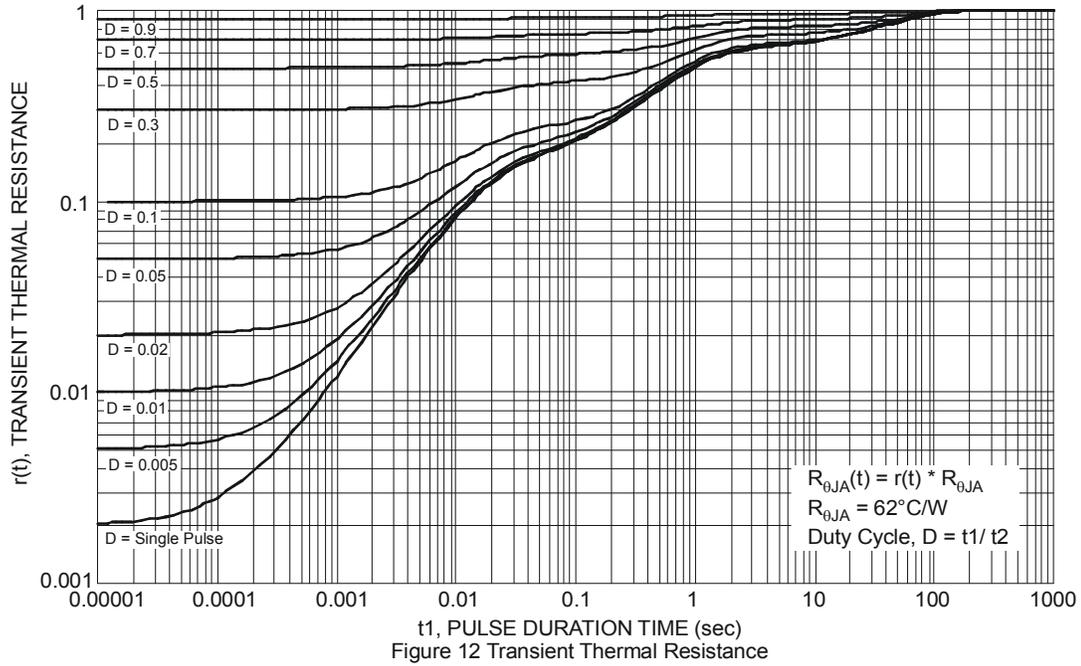
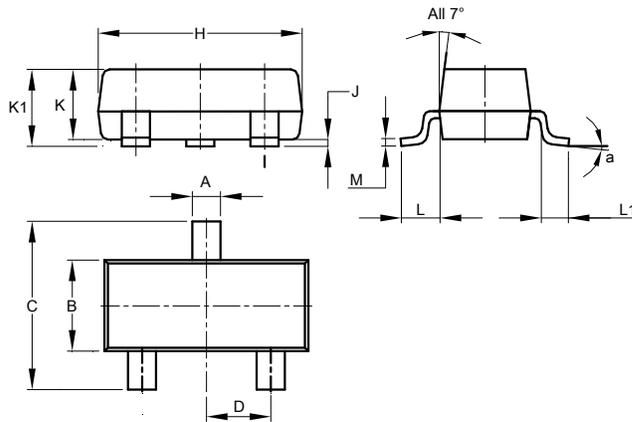


Figure 11 SOA, Safe Operation Area



### Package Outline Dimensions

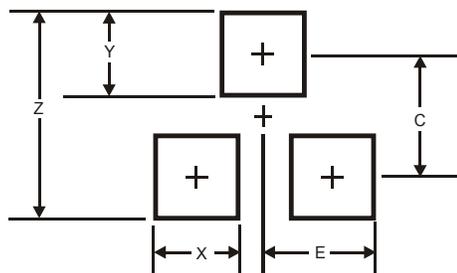
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

### Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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